

PDFN 3×3-8L

Complementary Enhancement MOSFET in a PDFN3×3-8L Plastic Package.

**N-channel**
 $V_{DS}(V)=30V$   $I_D=37A$ 
 $R_{DS(ON)}@10V<8m$  (Typ.7.5mR)

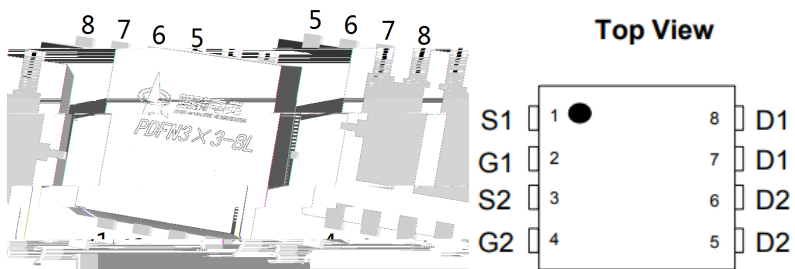
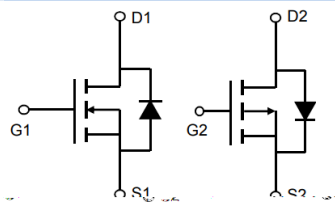
 $R_{DS(ON)}@4.5V<15m$  (Typ.11mR)

HF Product.

**P-channel**
 $V_{DS}(V)=-30V$   $I_D=-26A$ 
 $R_{DS(ON)}@-10V<13m$  (Typ.12mR)

 $R_{DS(ON)}@-4.5V<20m$  (Typ.17mR)

Battery protection switch, Mobile device battery charging and discharging, Load switch.

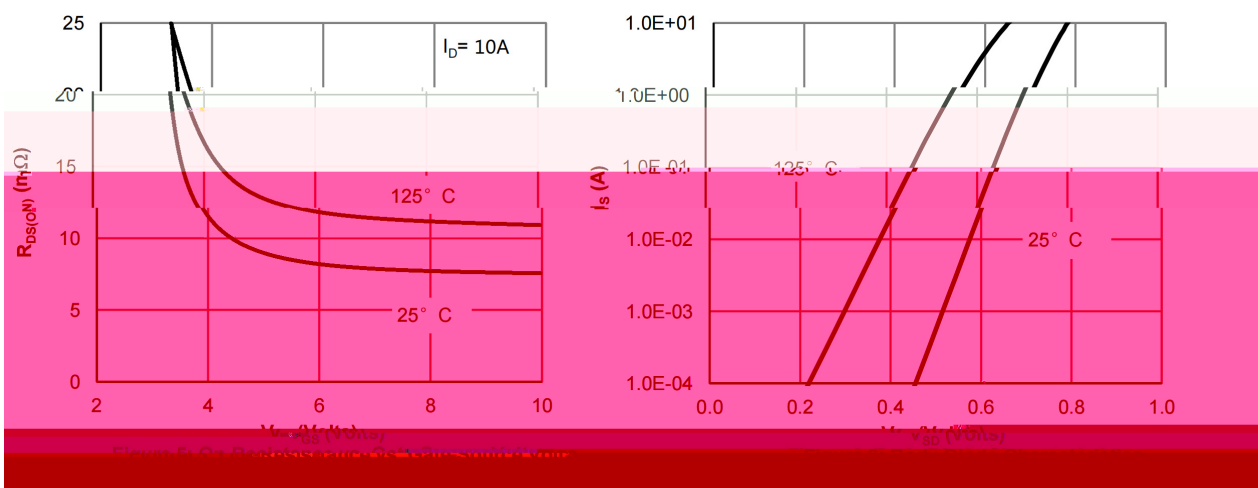
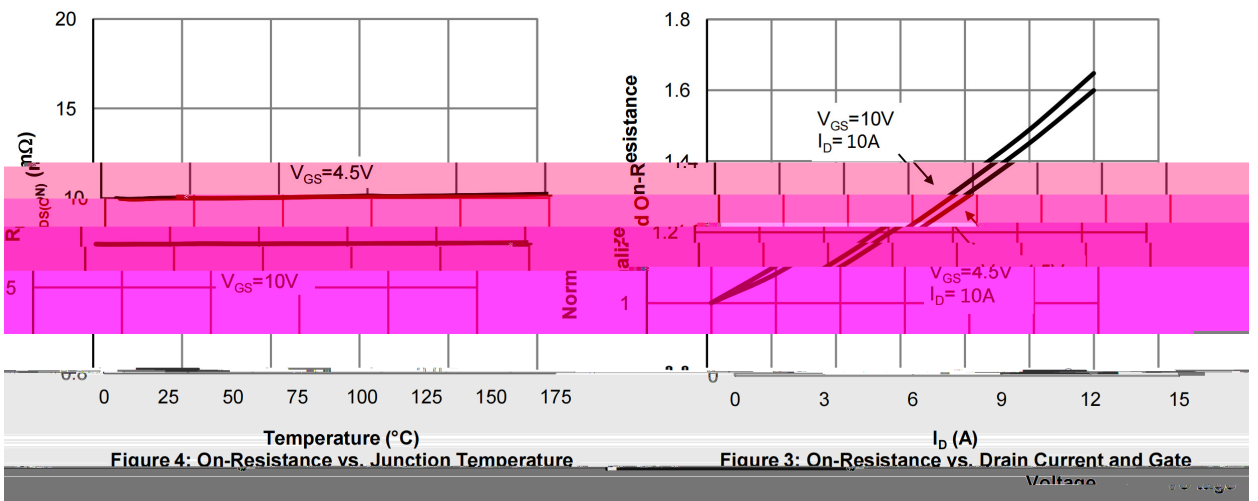
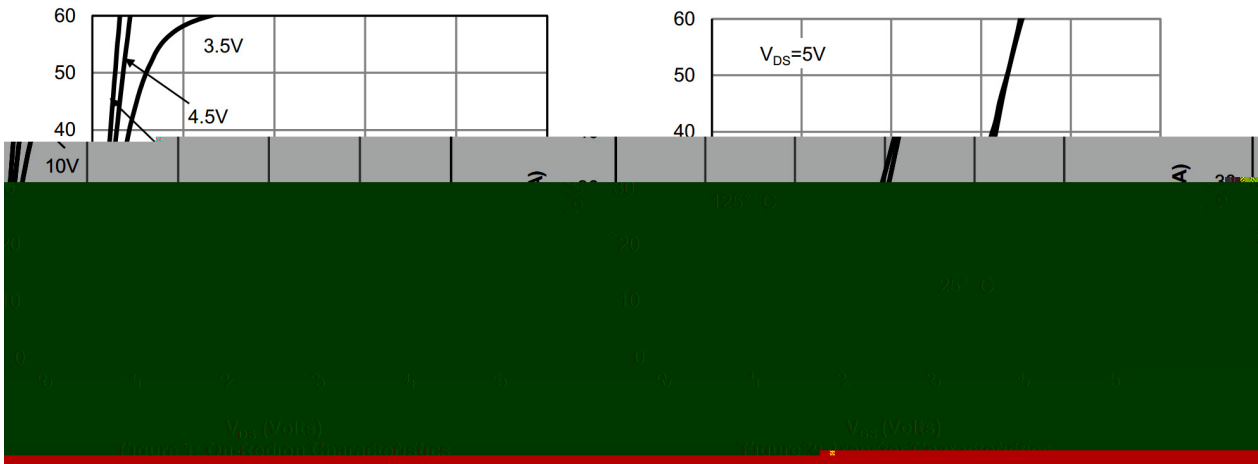


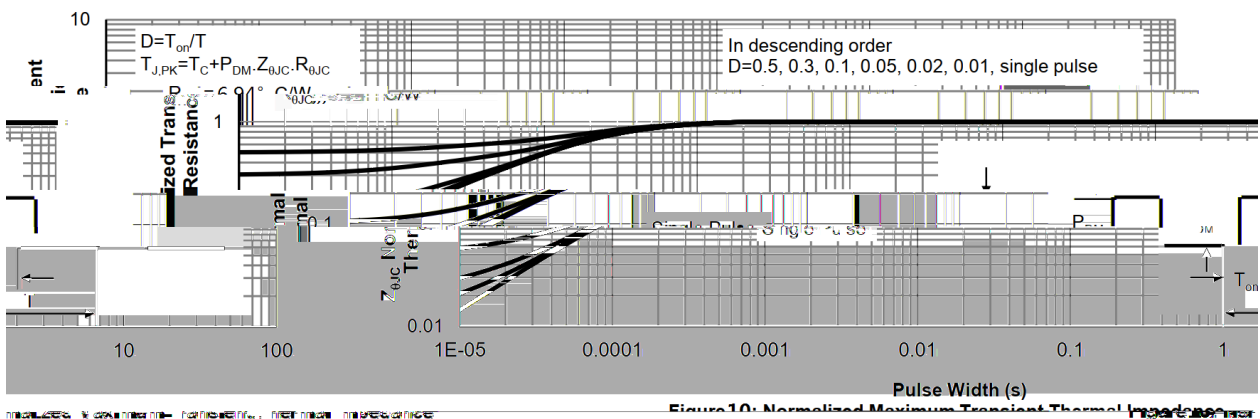
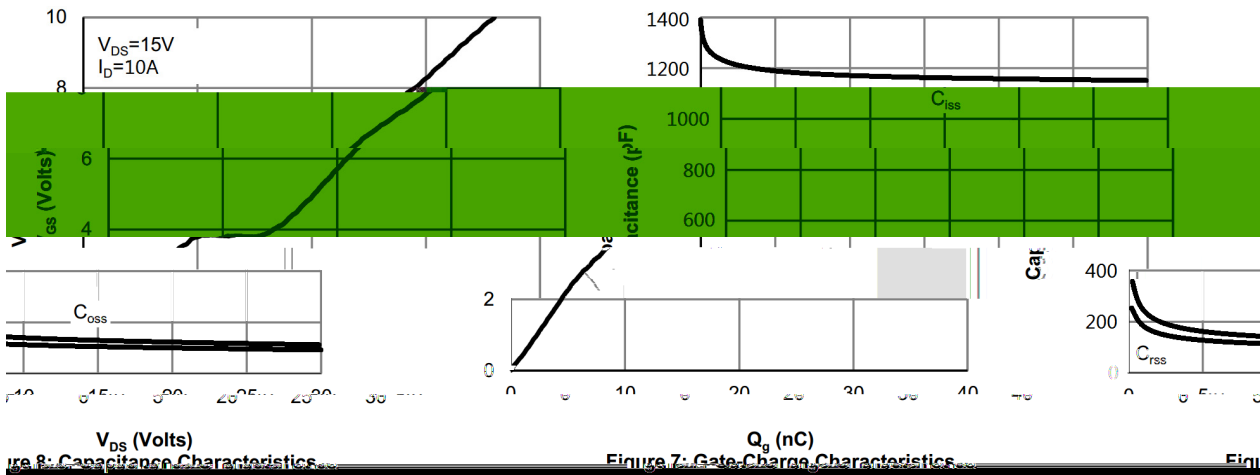
See Marking Instructions.

| Parameter                              | Symbol         | Rating      |            | Unit |
|--|----------------|-------------|------------|------|
|  |                | N-channe    | P-channell |      |
| Drain-Source Voltage                   | $V_{DSS}$      | 30          | -30        | V    |
| Gate-Source Voltage                    | $V_{GSS}$      | ±20         |            | V    |
| Continuous Drain Current               | $I_D(T_c=25)$  | 37          | -26        | A    |
| Pulsed Drain Current                   | $I_{DM}$       | 82          | -58        | A    |
| Power Dissipation                      | $P_D(T_c=25)$  | 18          | 15         | W    |
| Junction and Storage Temperature Range | $T_J, T_{STG}$ | -55 to +150 |            |      |
| Maximum Junction-to-Case               | $R_{JA}$       | 6.9         | 8.3        | /W   |

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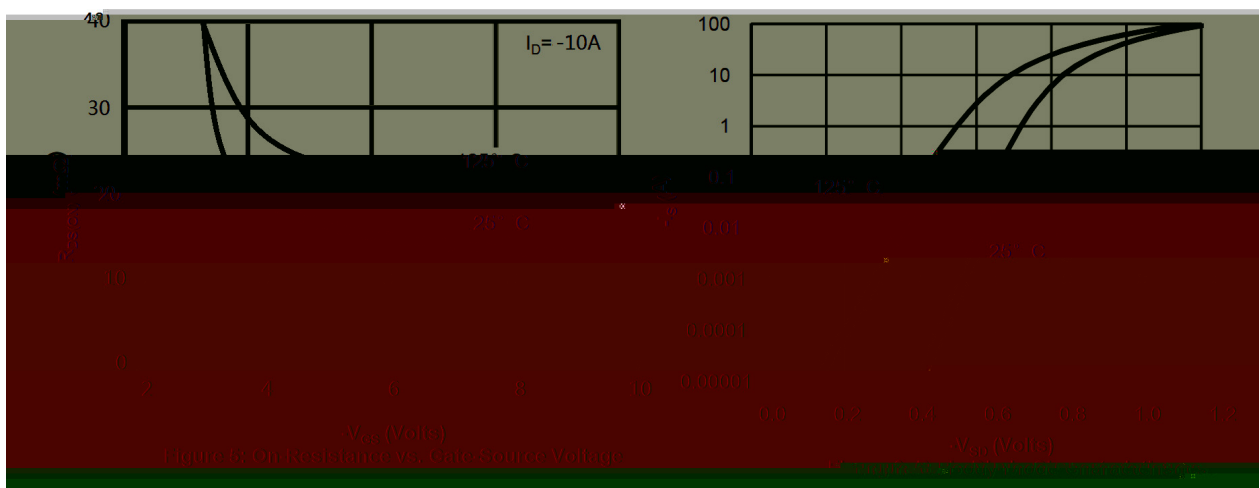
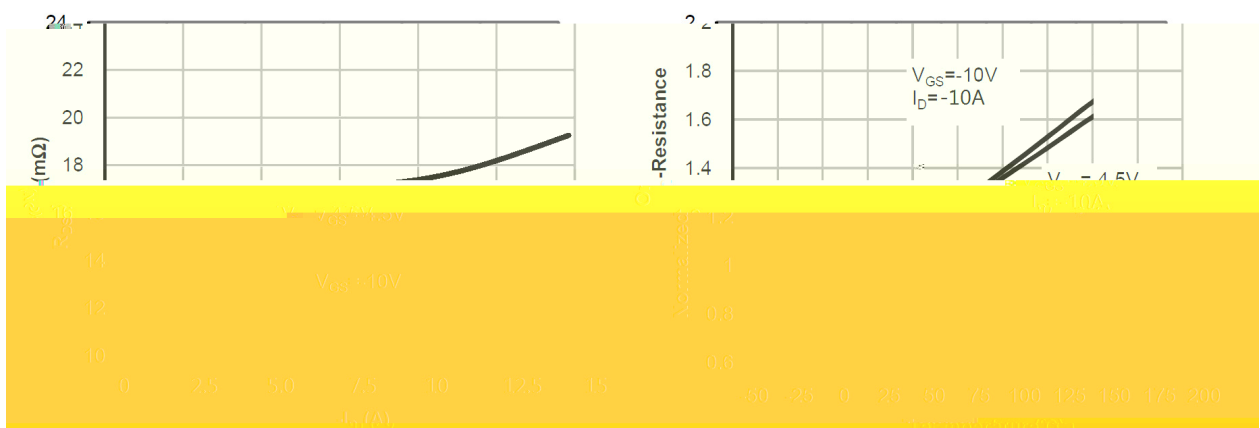
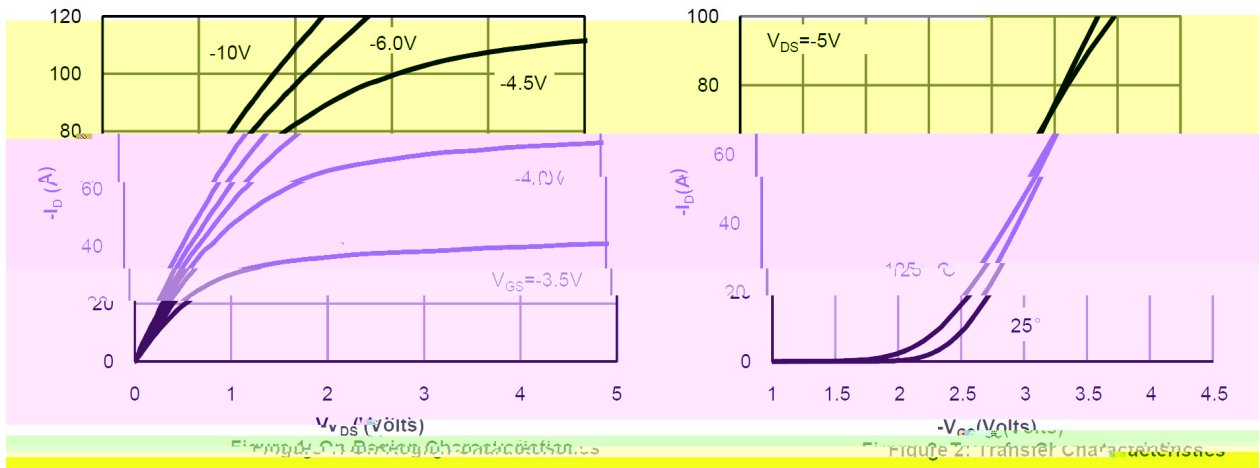
| Parameter                         | Symbol        | Test Conditions                                     | Min | Typ  | Max       | Unit    |
|-----------------------------------|---------------|---|-----|------|-----------|---------|
| Drain-Source Breakdown Voltage    | $BV_{DSS}$    | $V_{GS}=0V$ $I_D=250\mu A$                          | 30  | 35.5 |           | V       |
| Zero Gate Voltage Drain Current   | $I_{DSS}$     | $V_{DS}=30V$ $V_{GS}=0V$                            |     |      | 1.0       | $\mu A$ |
| Gate-Body leakage current         | $I_{GSS}$     | $V_{GS}=\pm 20V$ $V_{DS}=0V$                        |     |      | $\pm 100$ | nA      |
| Gate Threshold Voltage            | $V_{GS(th)}$  | $V_{DS}=V_{GS}$ $I_D=250\mu A$                      | 1.0 | 1.8  | 2.5       | V       |
| Static Drain-Source On-Resistance | $R_{DS(on)}$  | $V_{GS}=10V$ $I_D=10A$                              |     | 7.5  | 8         | m       |
|                                   |               | $V_{GS}=4.5V$ $I_D=10A$                             |     | 11   | 15        | m       |
| Diode Forward Voltage             | $V_{SD}$      | $V_{GS}=0V$ $I_S=1.0A$                              |     |      | 1.4       | V       |
| Input Capacitance                 | $C_{iss}$     | $V_{DS}=25V$ $V_{GS}=0V$<br>$f=1.0MHz$              |     | 1170 |           | pF      |
| Output Capacitance                | $C_{oss}$     |   |     | 110  |           | pF      |
| Reverse Transfer Capacitance      | $C_{rss}$     |   |     | 100  |           | pF      |
| Gate resistance                   | $R_g$         | $V_{DS}=0V$ $V_{GS}=0V$<br>$f=1.0MHz$               |     | 3.7  |           |         |
| Total Gate Charge                 | $Q_{g(10V)}$  | $V_{GS}=10V$ $V_{DS}=15V$<br>$I_D=10A$              |     | 40   |           | nC      |
| Total Gate Charge                 | $Q_{g(4.5V)}$ |   |     | 22   |           | nC      |
| Gate-Source Charge                | $Q_{gs}$      |   |     | 11   |           | nC      |
| Gate-Drain Charge                 | $Q_{gd}$      |   |     | 5    |           | nC      |
| Turn-On Delay Time                | $t_{d(on)}$   | $V_{DS}=15V$ $V_{GS}=10V$<br>$R_L=0.75$ $R_{GEN}=3$ |     | 11   |           | ns      |
| Turn-On Rise Time                 | $t_r$         |   |     | 14   |           | ns      |
| Turn-Off Delay Time               | $t_{d(off)}$  |   |     | 38   |           | ns      |
| Turn-Off Fall Time                | $t_f$         |   |     | 10   |           | ns      |

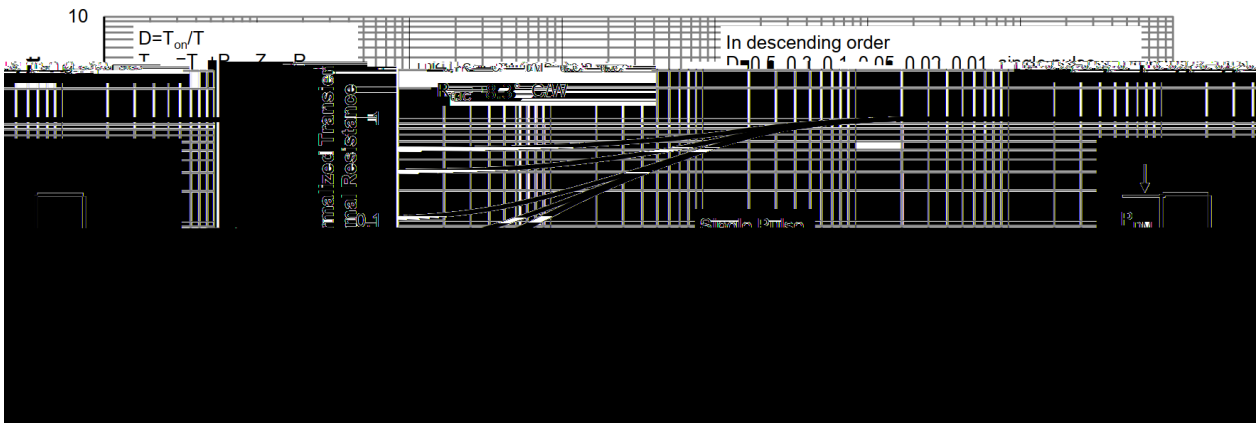
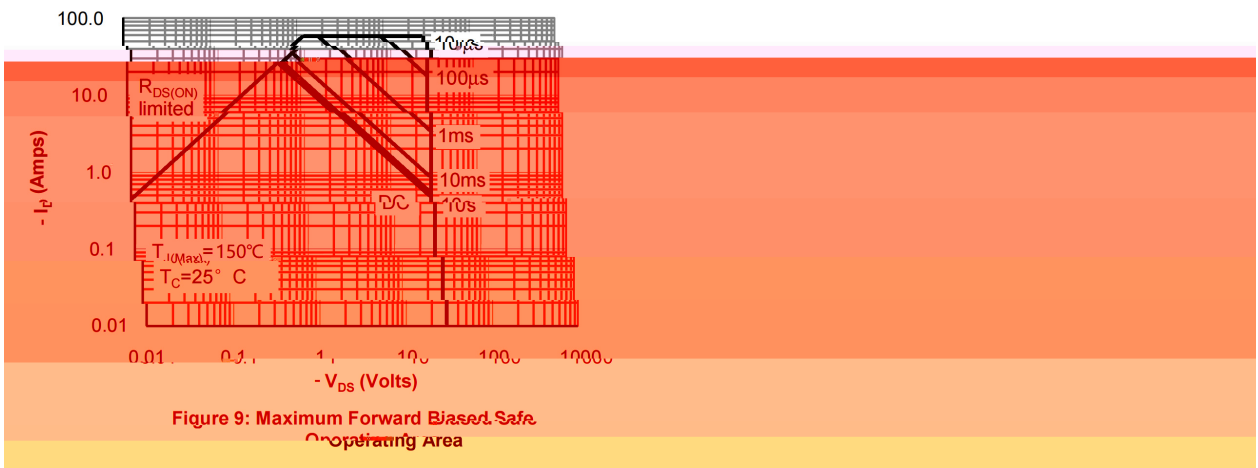
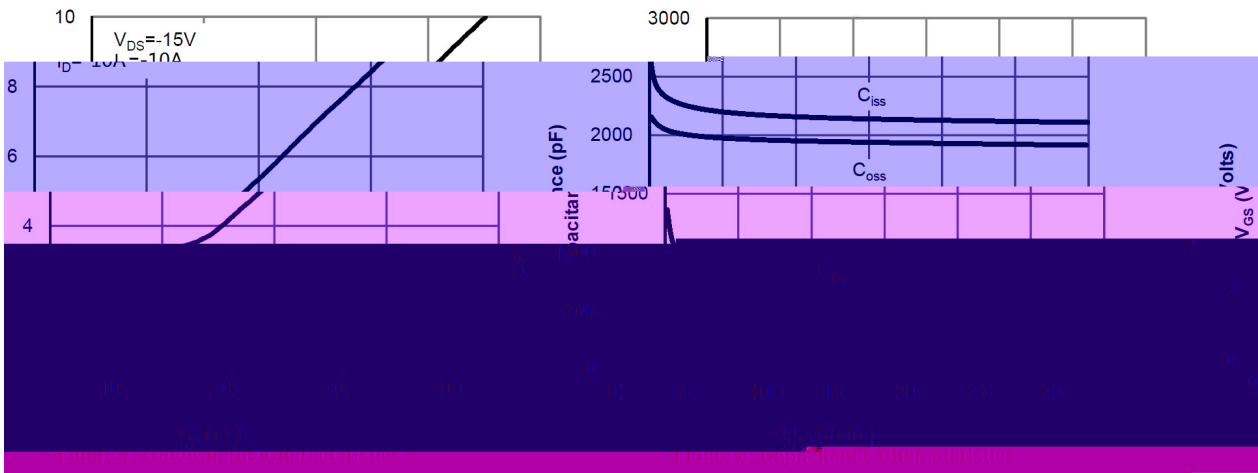




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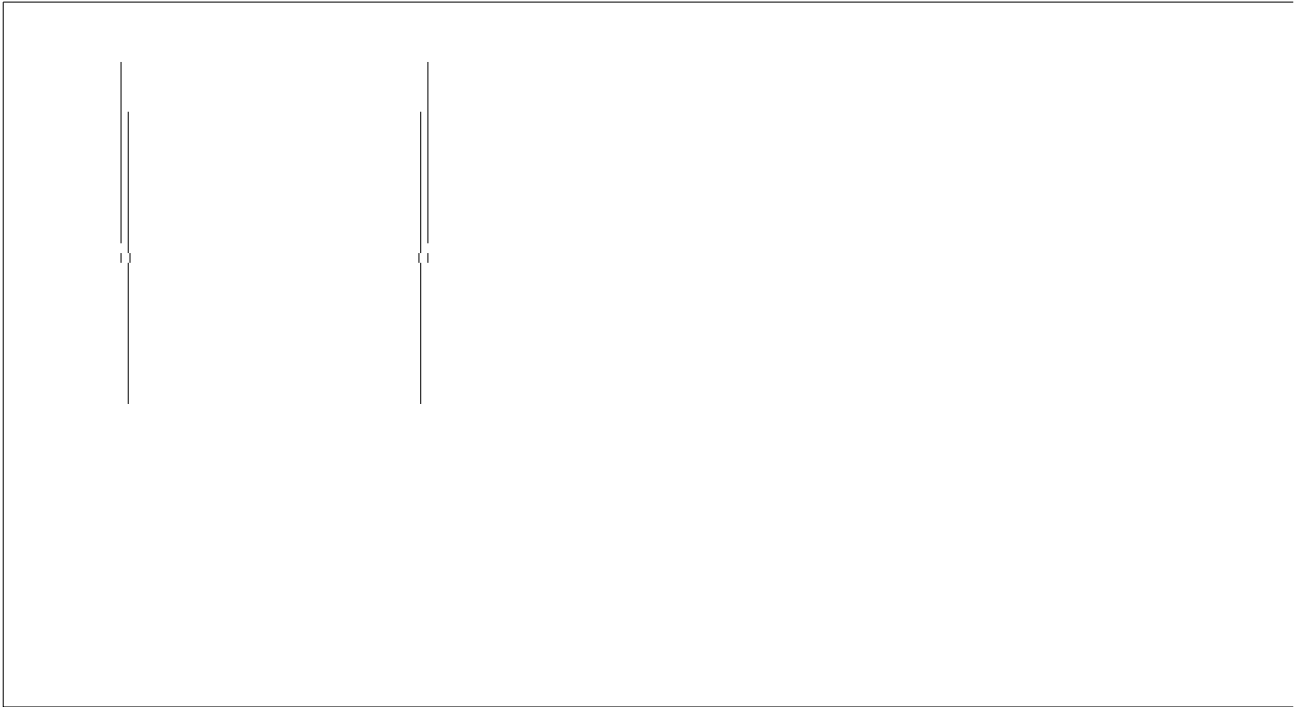
| Parameter                         | Symbol               | Test Conditions   | Min  | Typ  | Max  | Unit |
|-----------------------------------|----------------------|---|------|------|------|------|
| Drain-Source Breakdown Voltage    | BV <sub>DSS</sub>    | V <sub>GS</sub> =0V I <sub>D</sub> =-250μA  | -30  |      |      | V    |
| Zero Gate Voltage Drain Current   | I <sub>DSS</sub>     | V <sub>DS</sub> =-30 V <sub>GS</sub> =0V  |      |      | -1.0 | μA   |
| Gate-Body leakage current         | I <sub>GSS</sub>     | V <sub>GS</sub> =±20V V <sub>DS</sub> =0V   |      |      | ±100 | nA   |
| Gate Threshold Voltage            | V <sub>GS(th)</sub>  | V <sub>DS</sub> =V <sub>GS</sub> I <sub>D</sub> =-250μA                               | -1.0 | -1.5 | -2.5 | V    |
| Static Drain-Source On-Resistance | R <sub>DS(on)</sub>  | V <sub>GS</sub> =-10V I <sub>D</sub> =-10A  |      | 12   | 13   | m    |
|                                   |                      | V <sub>GS</sub> =-4.5V I <sub>D</sub> =-10A   |      | 17   | 20   | m    |
| Diode Forward Voltage             | V <sub>SD</sub>      | V <sub>GS</sub> =0V I <sub>S</sub> =-1.0A   |      |      | -1.4 | V    |
| Input Capacitance                 | C <sub>iss</sub>     | V <sub>DS</sub> =-25V V <sub>GS</sub> =0V<br>f=1.0MHz                                 |      | 2100 |      | pF   |
| Output Capacitance                | C <sub>oss</sub>     |   |      | 1900 |      | pF   |
| Reverse Transfer Capacitance      | C <sub>rss</sub>     |   |      | 640  |      | pF   |
| Gate resistance                   | R <sub>g</sub>       | V <sub>DS</sub> =0V V <sub>GS</sub> =0V<br>f=1.0MHz                                   |      | 4    |      |      |
| Total Gate Charge                 | Q <sub>g(10V)</sub>  | V <sub>GS</sub> =-10V V <sub>DS</sub> =-15V<br>I <sub>D</sub> =-10A                   |      | 35   |      | nC   |
| Total Gate Charge                 | Q <sub>g(4.5V)</sub> |   |      | 17   |      | nC   |
| Gate-Source Charge                | Q <sub>gs</sub>      |   |      | 5.7  |      | nC   |
| Gate-Drain Charge                 | Q <sub>gd</sub>      |   |      | 8.8  |      | nC   |
| Turn-On Delay Time                | t <sub>d(on)</sub>   | V <sub>DS</sub> =-15 V V <sub>GS</sub> =-10V<br>R <sub>L</sub> =1 R <sub>GEN</sub> =3 |      | 11   |      | ns   |
| Turn-On Rise Time                 | t <sub>r</sub>       |   |      | 7.5  |      | ns   |
| Turn-Off Delay Time               | t <sub>d(off)</sub>  |   |      | 43.5 |      | ns   |
| Turn-Off Fall Time                | t <sub>f</sub>       |   |      | 17.5 |      | ns   |

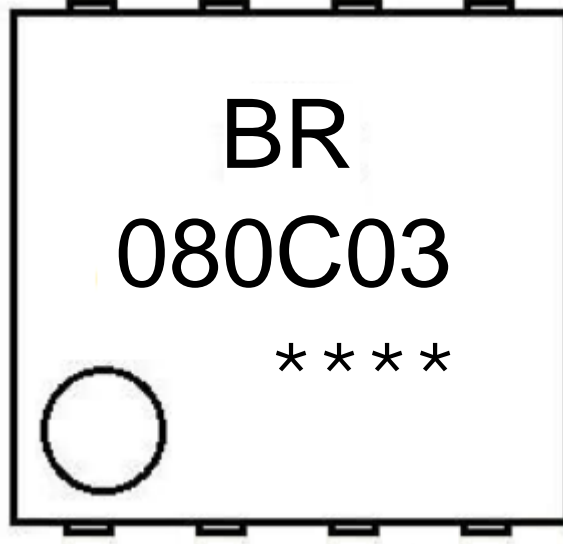




PDFN3X3-8L

Unit:mm





BR

080C03

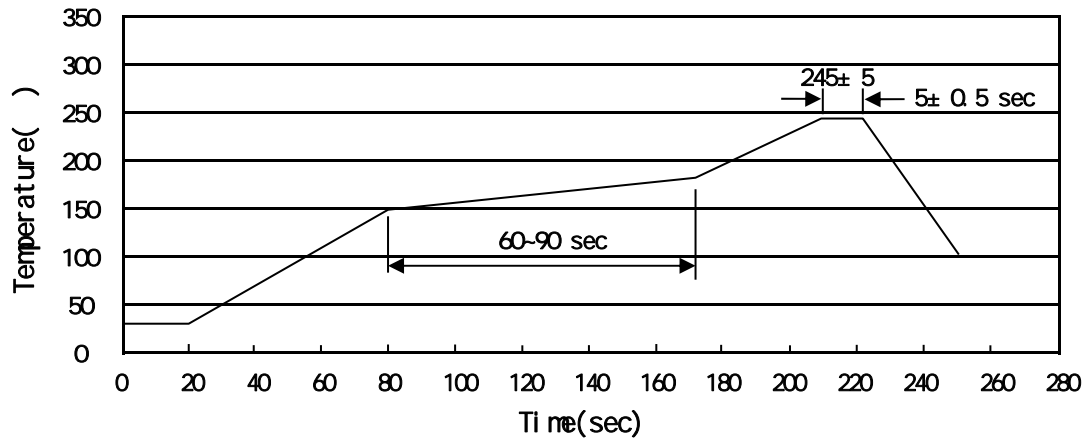
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Note:

BR: Company Code

080C03: Product Type Code

\*\*\*\*: Lot No. Code, code change with Lot No

**Temperature Profile for IR Reflow Soldering(Pb-Free)**


Note:

- |   |       |     |    |           |   |
|---|-------|-----|----|-----------|---|
| 1 | 150   | 180 | 60 | 90sec;    | 1.Preheating:150~180 , Time:60~90sec.   |
| 2 | 245±5 |     |    | 5±0.5sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 |       |     | 2  | 10 /sec.  | 3. Cooling Speed: 2~10 /sec.            |

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

| Package Type | Units |   |        |   |        | Dimension (unit mm <sup>3</sup> ) |     |            |             |
|--------------|-------|---|--------|---|--------|-----------------------------------|-----|------------|-------------|
|              |       |   |        |   |        |                                   |     |            |             |
| PDFN3x3-8L   | 5,000 | 2 | 10,000 | 6 | 60,000 | 13                                | x12 | 360x360x50 | 380x335x366 |